

**Amendments to the Specification:**

Please replace the Abstract with the attached amended Abstract.

Please replace the paragraph beginning on page 8, line 4, with the following rewritten paragraph:

In order to achieve the aforementioned object, according to the present invention, there is provided an SOI wafer in which at least a silicon active layer is formed on a support substrate, wherein at least the silicon active layer consists of silicon single crystal grown by ~~Chechralski~~-Czochralski method, which is occupied by N region outside OSF generated in a shape of a ring and has no defect region detected by Cu deposition method.

Please replace the paragraph beginning on page 10, line 8, with the following rewritten paragraph:

Moreover, in the present invention, there is also provided a method for producing an SOI wafer as follows. Namely, there is provided a method for producing an SOI wafer comprising steps of, in a bond wafer that is to be a silicon active layer and a base wafer that is to be a support substrate, implanting hydrogen ions, rare gas ions or mixture gas ions of these gases from a surface of the bond wafer to form an ion-implanted layer inside the bond wafer, bonding the surface of the ion-implanted side of the bond wafer and a surface of the base wafer via an oxide film or directly, and subsequently delaminating a part of the bond wafer at the ion-implanted layer by heat treatment to form an SOI wafer, wherein a silicon wafer consisting of silicon single crystal grown by ~~Chechralski~~-Czochralski method, which is occupied by N region outside OSF generated in a shape of a ring and has no defect region detected by Cu deposition method, is used as the bond wafer.